



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Tomohiro Kawase et al. Art Unit : 1765
Serial No. : 09/824,965 Examiner : Robert Kunemund
Filed : April 3, 2001
Title : METHOD OF PREPARING GROUP III-V COMPOUND SEMICONDUCTOR CRYSTAL

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

FOURTH INFORMATION DISCLOSURE STATEMENT

Applicant submits herewith a Form PTO-1449 together with the following documents:

1. Communication from the European Patent Office ("EPO") dated October 15, 2003, informing applicant's agent of an opposition to applicant's EP application 97106815.0, which claims the same priority as the present application.
2. "Einspruch gegen ein europäisches Patent" (Opposition against a European patent) (in German).
3. Translation into English of the Substantiation of the Opposition (part of item 2 above).
4. Hein, "Growth of Semiinsulating GaAs Crystals by Vertical Gradient Freeze Technique," Crystal Research Technology v. 30, No. 7, pp. 897-909 (1995) (Opposition Reference D1).
5. Hein et al, "Die Kristallisation and Schmelzen aus metallurgischer Prozess," Metall, v. 47, No. 10, pp. 924-928 (Oct. 1993) (Opposition Reference D1A).
6. Flade, "Entwicklung gross flächriger GaAs-Substrate," Freiberger Elektronikwerkstoffe GmbH (the opposer) (Opposition Reference D2).
7. Partial translation into English of item 5 (Opposition Reference D1A).
8. Partial translation into English of item 6 (Opposition Reference D2).
9. Copy of July 1, 2003 letter from Universitätsbibliotek Hannover.... (Opposition Reference D2A).

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Attorney's Docket No.: 12967-002001 / 997047-06
(TM/it)

Due to the bulk of one of these documents, they are being hand delivered to the PTO.

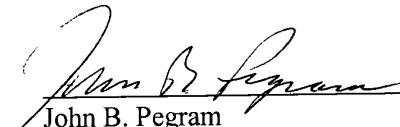
Applicant's detailed Comments will follow by facsimile in the near future.

Applicant has used the same document designations on Form PTO-1449 as were used in the EP Opposition, to avoid confusion.

Pursuant to 37 C.F.R. §1.97(e), Applicant states that each item of information contained in the information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this information disclosure statement. Therefore, pursuant to 37 CFR §1.97(c)(1), no IDS filing fee is required.

Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

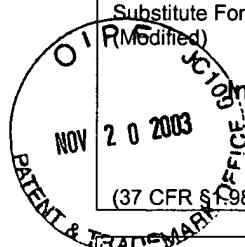


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Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12967-002001	Application No. 09/824,965
Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR § 1.98(b))		Applicant Tomohiro Kawase et al.	
		Filing Date April 3, 2001	Group Art Unit 1765

U.S. Patent Documents

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AL							
	AM							
	AN							
	AO							
	AP							

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
	D1	Hein, "Growth of Semiinsulating GaAs Crystals by Vertical Gradient Freeze Technique," Crystal Research Technology v. 30, No. 7, pp. 897-909 (1995)
	D1A	Hein et al, "Die Kristallisation und Schmelzen aus metallurgischer Prozess," Metall, v. 47, No. 10, pp. 924-928 (Oct. 1993)
	D2	Flade, "Entwicklung gross flächriger GaAs-Substrate," Freiberger Elektronikwerkstoffe GmbH (Hannover, Germany, February 19, 1996) (?)

Examiner Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	